IN THE CLAIMS:

Please cancel Claim 43 without prejudice to or disclaimer of the subject matter presented therein. Please amend Claims 42 and 44, and add new Claims 46 to 50 as shown below. The claims, as pending in the subject application, read as follows:

1 to 41. (Cancelled)

42. (Currently Amended) A photoelectric conversion device comprising:

an electron acceptive charge transfer ~~layer~~ region;

an electron donative charge transfer ~~layer~~ region; and

a light absorption ~~layer~~ region existing between the charge transfer ~~layers~~ regions,

wherein the light absorption ~~layer contains~~ region is a semiconductor, and either of the charge transfer ~~layers~~ regions is a semiconductor acicular crystal ~~layer~~ region comprising an aggregate of acicular crystals, and

wherein the acicular crystals comprise a metal oxide.

43. (Cancelled)

44. (Currently Amended) A photoelectric conversion device according to ~~claim 43~~ claim 42, wherein the metal oxide is titanium oxide, zinc oxide or tin oxide.

45. (Previously Presented) A photoelectric conversion device according to claim 42, wherein an aspect ratio of the acicular crystals is 5 or more when the aspect ratio is defined as the ratio of the length of the acicular crystals to the diameter of the acicular crystals or as the ratio of the length of the acicular crystals to the length of the shortest line in a transverse cross-section of the acicular crystals passing the gravity center of the acicular crystals.

46. (New) A photoelectric conversion device according to claim 42, wherein the light absorption region comprises an amorphous semiconductor or a direct transition type semiconductor.

47. (New) A photoelectric conversion device according to claim 42, wherein the acicular crystals bear particles.

48. (New) A photoelectric conversion device according to claim 42, wherein the acicular crystals are joined to a surface of a substrate and the angle between the axial direction of the acicular crystals and the surface of the substrate is 60 degrees or more.

49. (New) A photoelectric conversion device comprising:

an electron acceptive charge transfer region;

an electron donative charge transfer region; and

a light absorption region existing between the charge transfer regions,

wherein the light absorption region is a semiconductor, and either of the charge transfer regions is a semiconductor acicular crystal region comprising an aggregate of acicular crystals, and

wherein the acicular crystals comprise CuI or NiO.

50. (New) A photoelectric conversion device comprising:

an electron acceptive charge transfer region;

an electron donative charge transfer region; and

a light absorption region existing between the charge transfer regions,

wherein the light absorption region is a semiconductor, and either of the charge transfer regions is a semiconductor acicular crystal region comprising an aggregate of acicular crystals, and

wherein an aspect ratio of the acicular crystals is 10 or more when the aspect ratio is defined as the ratio of the length of the acicular crystals to the diameter of the acicular crystals or as the ratio of the length of the acicular crystals to the length of the shortest line in a transverse cross-section of the acicular crystals passing the gravity center of the acicular crystals.